

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	4mΩ @V _{GS} = 10V	75A
	7mΩ @V _{GS} = 4.5V	75A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On-State Losses
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

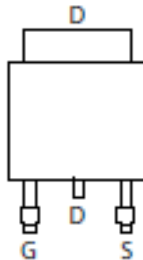
- Power Management Functions
- DC-DC Converters
- BLDC Motor control
- Reverse Polarity Protection

Mechanical Data

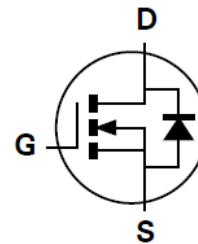
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.315 grams (Approximate)



Top View



Pin Out Top View



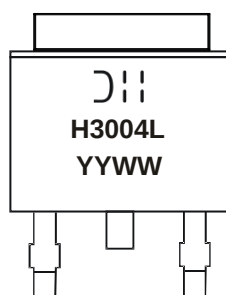
Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH3004LK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DII = Manufacturer's Marking
 H3004L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 16 = 2016)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	+20 -16	V
Continuous Drain Current V _{GS} = 10V	Steady State (Note 7)	T _C = +25°C T _C = +100°C	I _D	75 75	A
	Steady State (Note 6)	T _A = +25°C T _A = +100°C	I _D	21 15	A
Pulsed Drain Current (10μs Pulse, Duty Cycle=1%)			I _{DM}	105	A
Maximum Continuous Body Diode Forward Current			I _S	75	A
Avalanche Current L=5mH			I _{AS}	10.7	A
Avalanche Energy L=5mH			E _{AS}	287	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 7)	P _D	107	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	50	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	1.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 24V, V _{GS} = 0V
Zero Gate Voltage Drain Current (Note 9)	I _{DSS}	—	—	10	μA	V _{DS} = 24V, V _{GS} = 0V T _A = +125°C
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = +20V, V _{DS} = 0V V _{GS} = -16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.7	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.3	4	mΩ	V _{GS} = 10V, I _D = 20A
		—	5.5	7		V _{GS} = 4.5V, I _D = 7A
Diode Forward Voltage	V _{SD}	—	0.75	1	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	2,370	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	—	1,360	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	240	—	pF	
Gate Resistance	R _G	0.15	0.6	1.5	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	20	—	nC	V _{DS} = 15V, I _D = 20A
Total Gate Charge (V _{GS} = 10V)	Q _G	—	44	—	nC	
Gate-Source Charge	Q _{GS}	—	7	—	nC	
Gate-Drain Charge	Q _{GD}	—	8	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6.2	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 0.75Ω, R _G = 3Ω, I _D = 20A
Turn-On Rise Time	t _R	—	4.3	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	21	—	ns	
Turn-Off Fall Time	t _F	—	8	—	ns	
Reverse Recovery Time	t _{RR}	—	25	—	ns	I _F = 15A, di/dt = 500A/μs
Reverse Recovery Charge	Q _{RR}	—	37	—	nC	

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad)
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

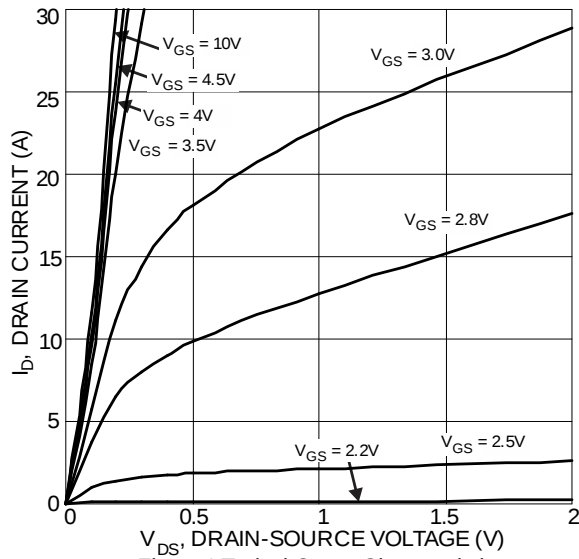


Figure 1 Typical Output Characteristic

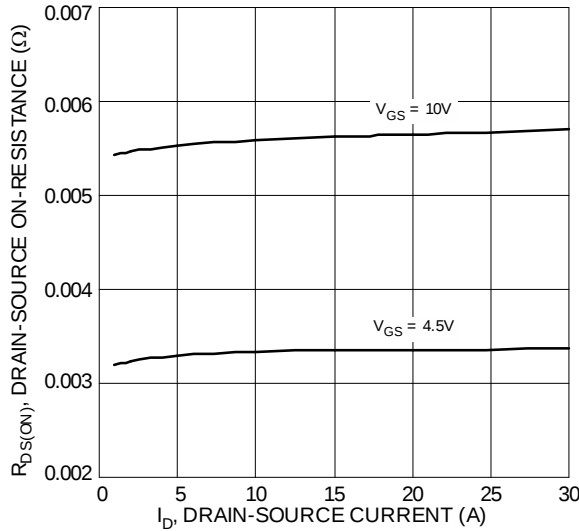


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

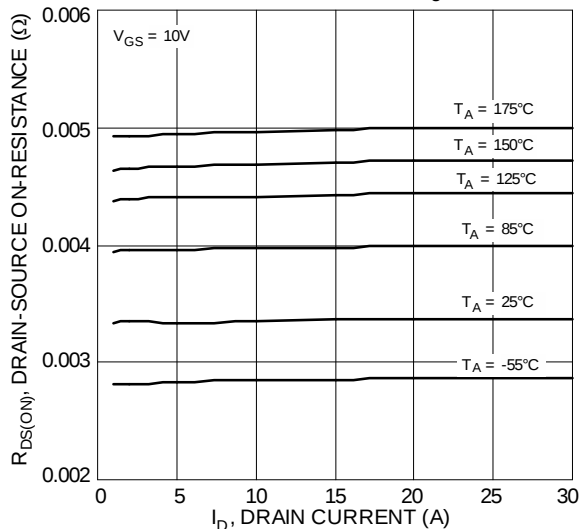


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

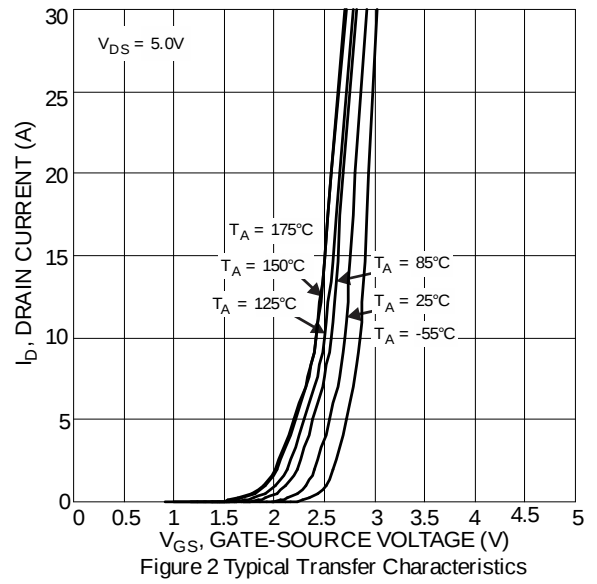


Figure 2 Typical Transfer Characteristics

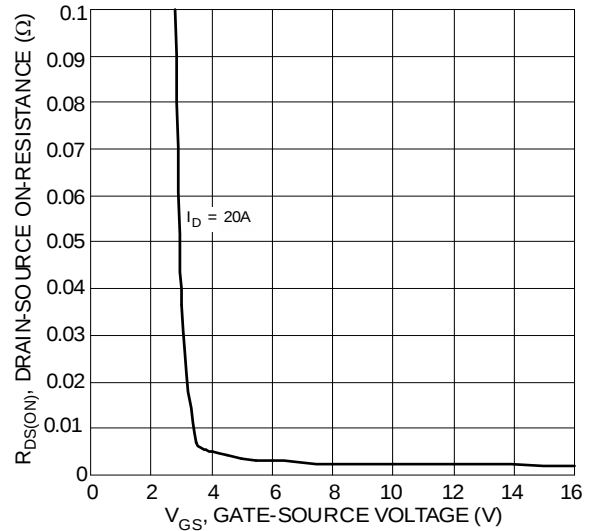


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

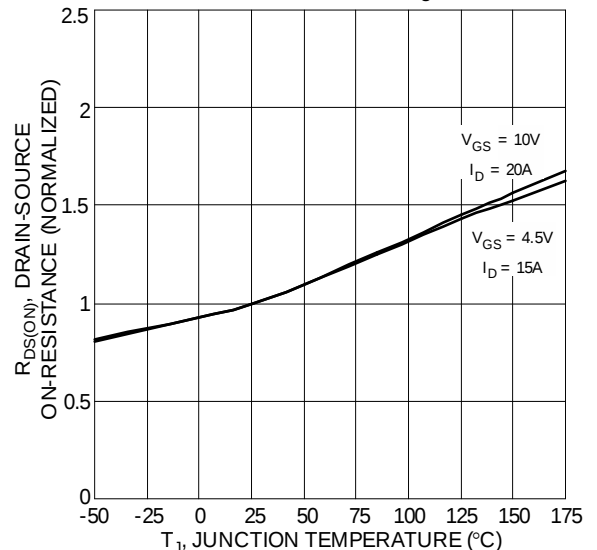
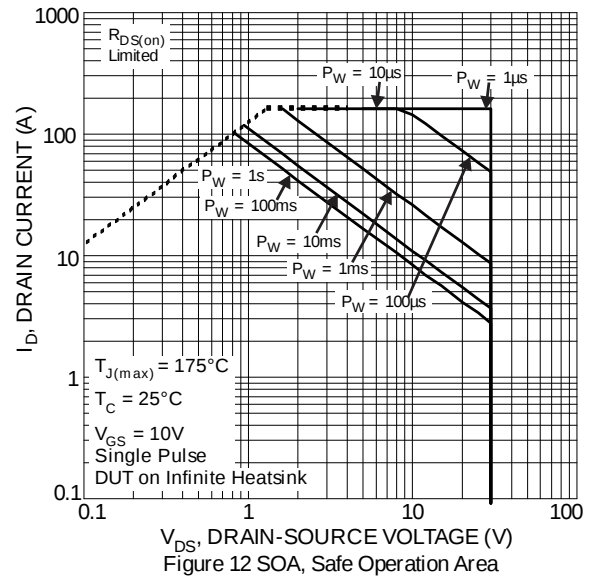
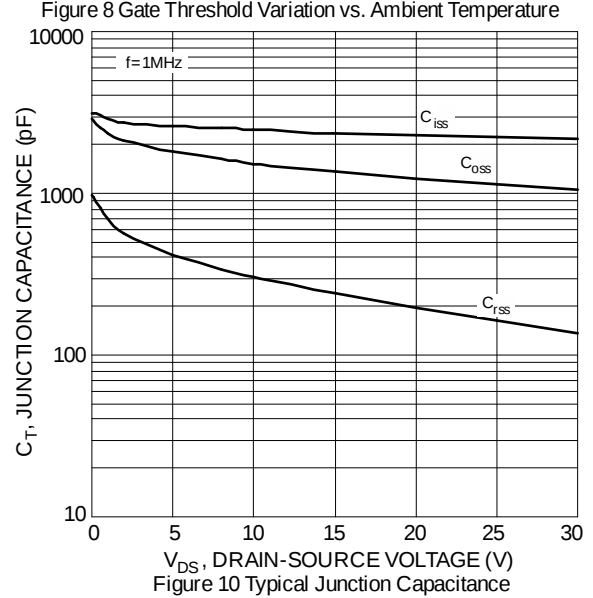
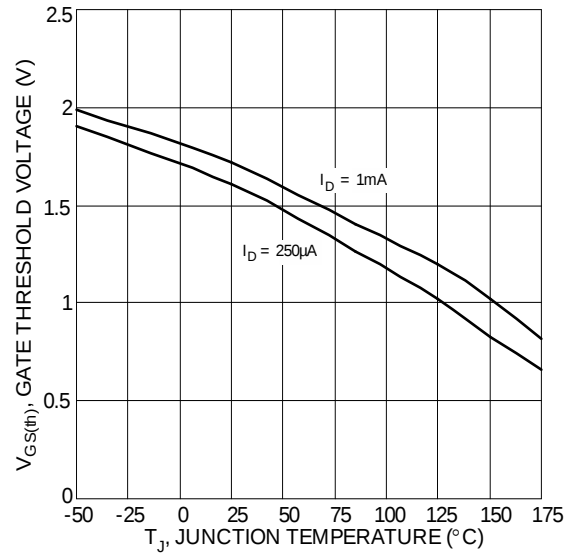
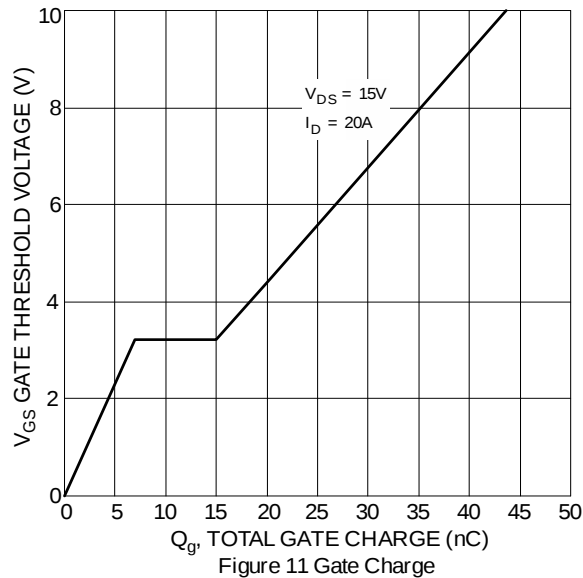
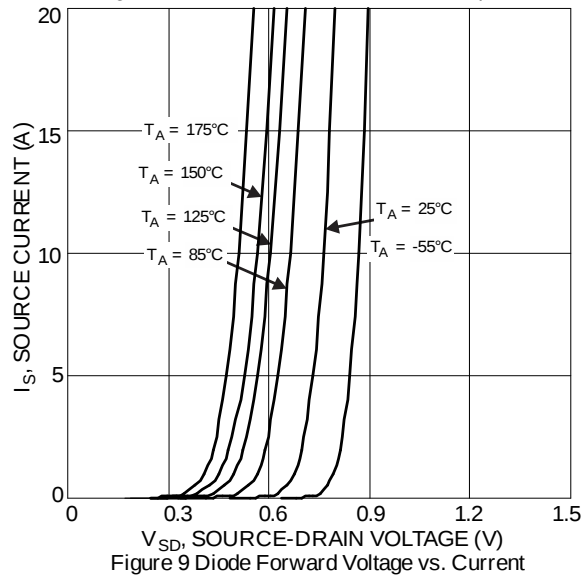
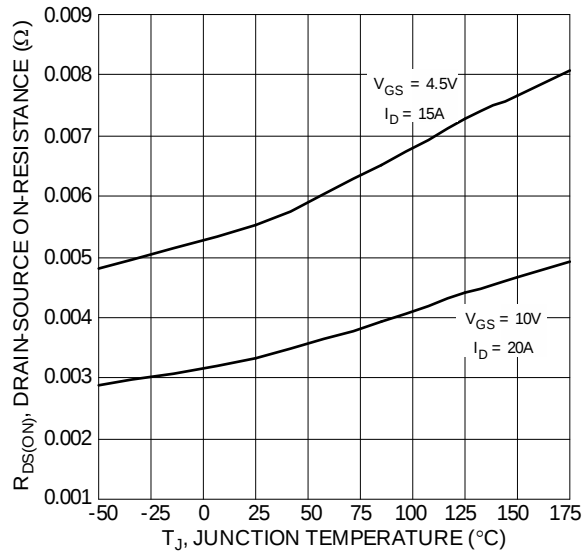
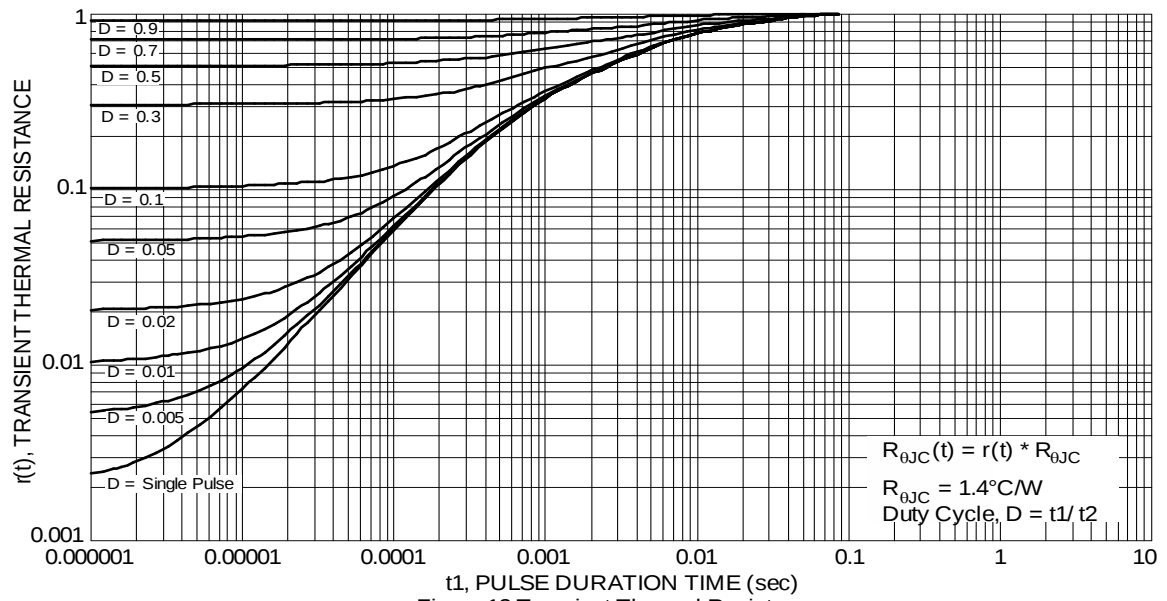


Figure 6 On-Resistance Variation with Temperature

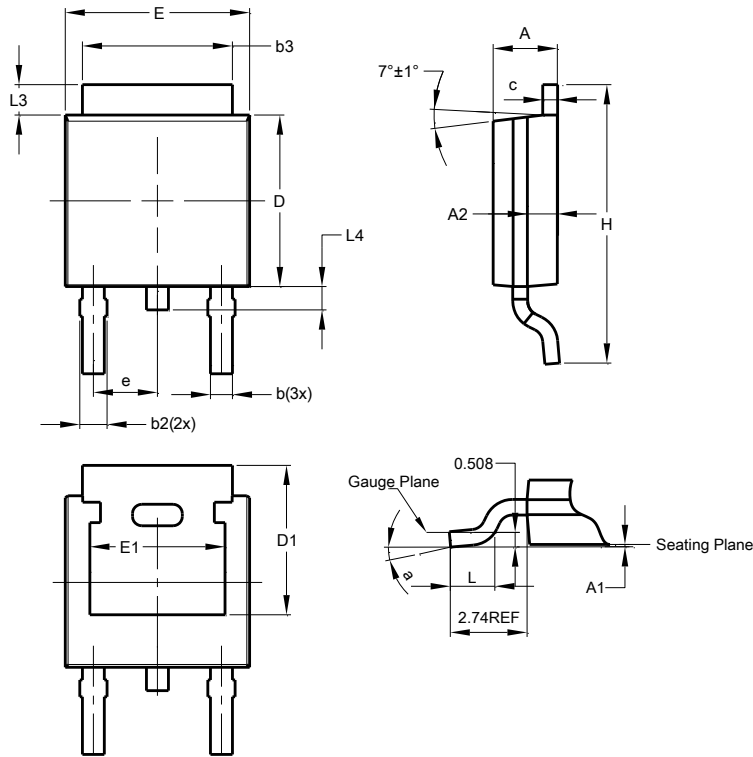




Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

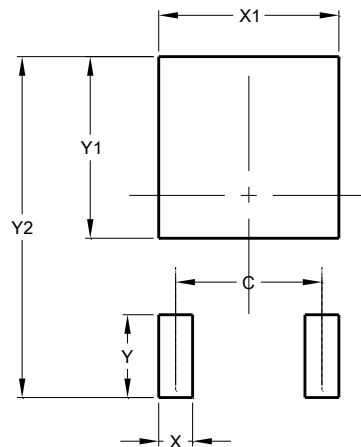


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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